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MINIWORKSHOP ON STRONG ELECTRON CORRELATIONS
"Disorder and Interaction in Quantum Systems
and Their Classical Analogs"

(1 - 19 July 1996)

"Vortex Pinning and Elementary Quantum Mechanics"

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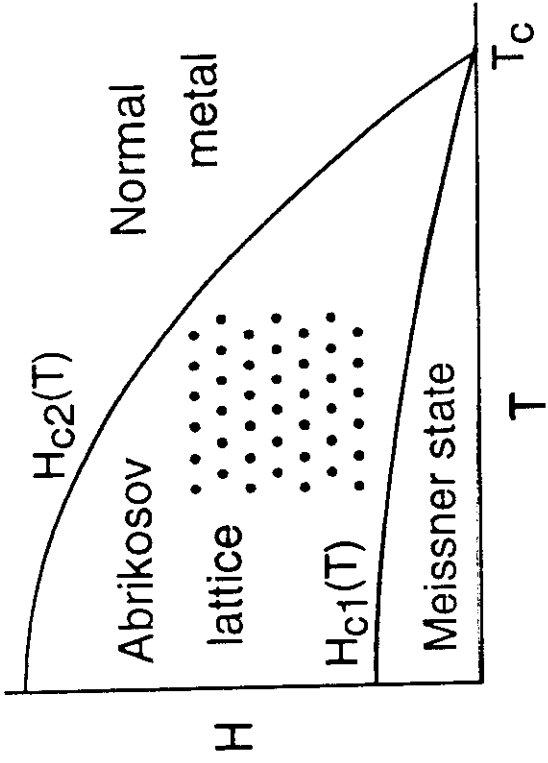
These are preliminary lecture notes, intended only for distribution to participants.

VORTEX PINNING
AND ELEMENTARY QUANTUM
MECHANICS

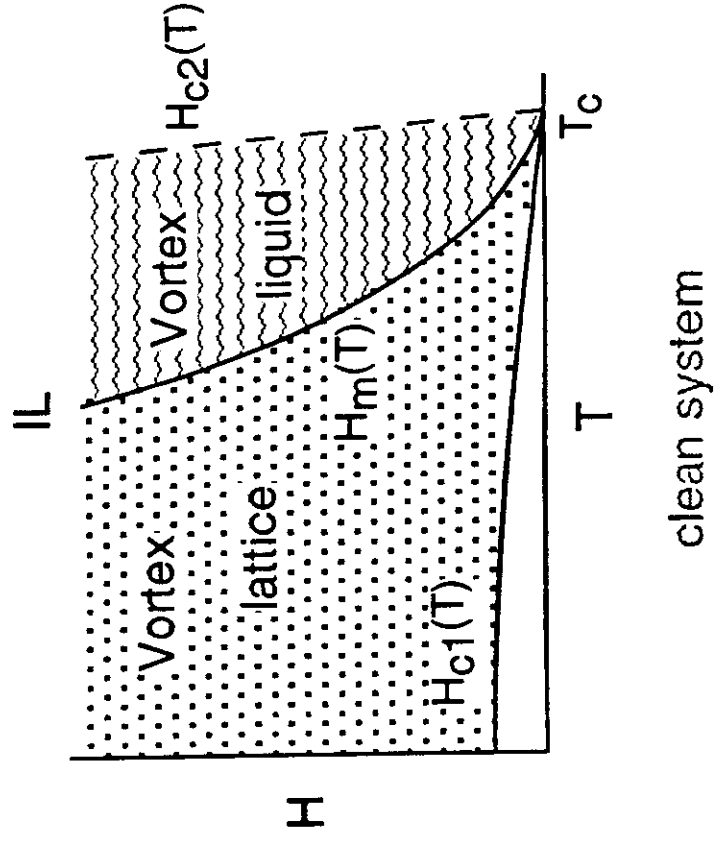
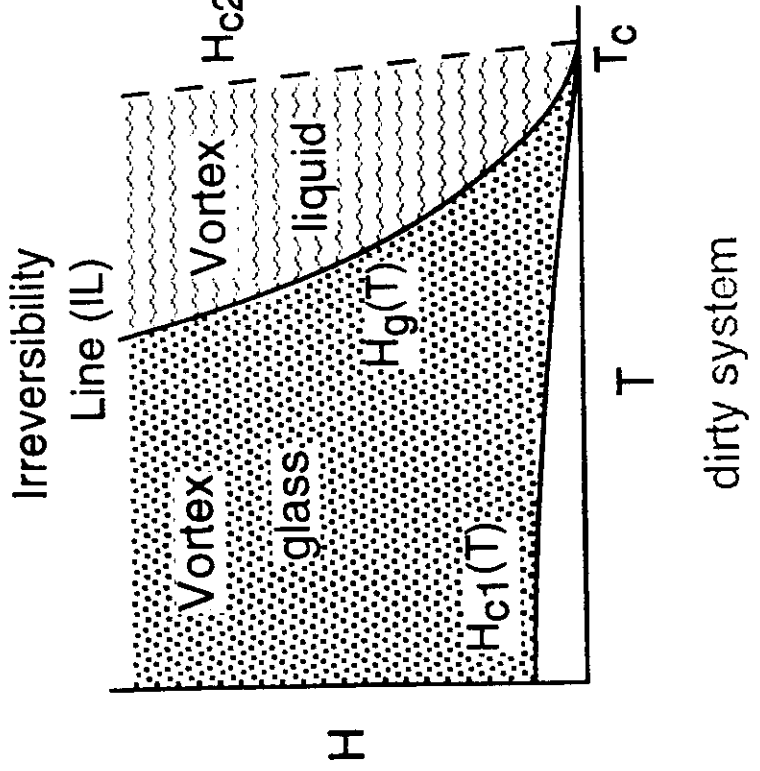
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Conventional superconductors:



High-temperature superconductors:



VORTEX / 2D-BOSON ANALOGY

Model free energy for N flux lines

$$F_N = \int_0^L dz \left\{ \sum_{i=1}^N \left[\frac{\epsilon_l}{2} \left| \frac{d\vec{r}_i(z)}{dz} \right|^2 + V_D(\vec{r}_i(z)) \right] + \frac{1}{2} \sum_{i \neq j} V[|\vec{r}_i(z) - \vec{r}_j(z)|] \right\}$$

$\{\vec{r}_i(z)\}$: vortex trajectories (magnetic field aligned with the z axis)

$V(|\vec{r}_i - \vec{r}_j|)$: the interaction potential between vortices

$\epsilon_l =$: the vortex linear tension
 $= \epsilon^2 \epsilon_0$ $\epsilon_0 = \left(\frac{\Phi_0}{4\pi\lambda} \right)^2$ $\lambda \equiv \lambda_{ab}$

ϵ : the material anisotropy

$V_D(\vec{r})$: the pinning potential modeled by a random array of identical cylindrical traps of average spacing d and radius r_0

a potential well depth: U_0

The partition function:

$$Z = \sum_{n=0}^{\infty} \frac{1}{n!} \sum_P e^{\mu n L / T} \int \mathcal{D}\vec{z}_1(z) \dots \int \mathcal{D}\vec{z}_n(z) e^{-F_N / T}$$

$\mu = \epsilon_L - H \phi_0 / 4\pi$: the chemical potential

Periodic boundary conditions are imposed on the system in the z direction

\sum_P : goes over all possible permutations of boundary conditions such that

$$\vec{z}_i(0) = \vec{z}_j(L)$$

Z is identical to an imaginary time Feynman path integral of a system of 2D bosons.

D.R. Nelson, PRL 60, 1943 (1988)

D.R. Nelson and H. S. Seung

PR B 39, 9153 (1989)

Boson mapping

2D bosons ↔ Vortices

Mass ↔ ϵ_L

\hbar ↔ T

\hbar/T ↔ L

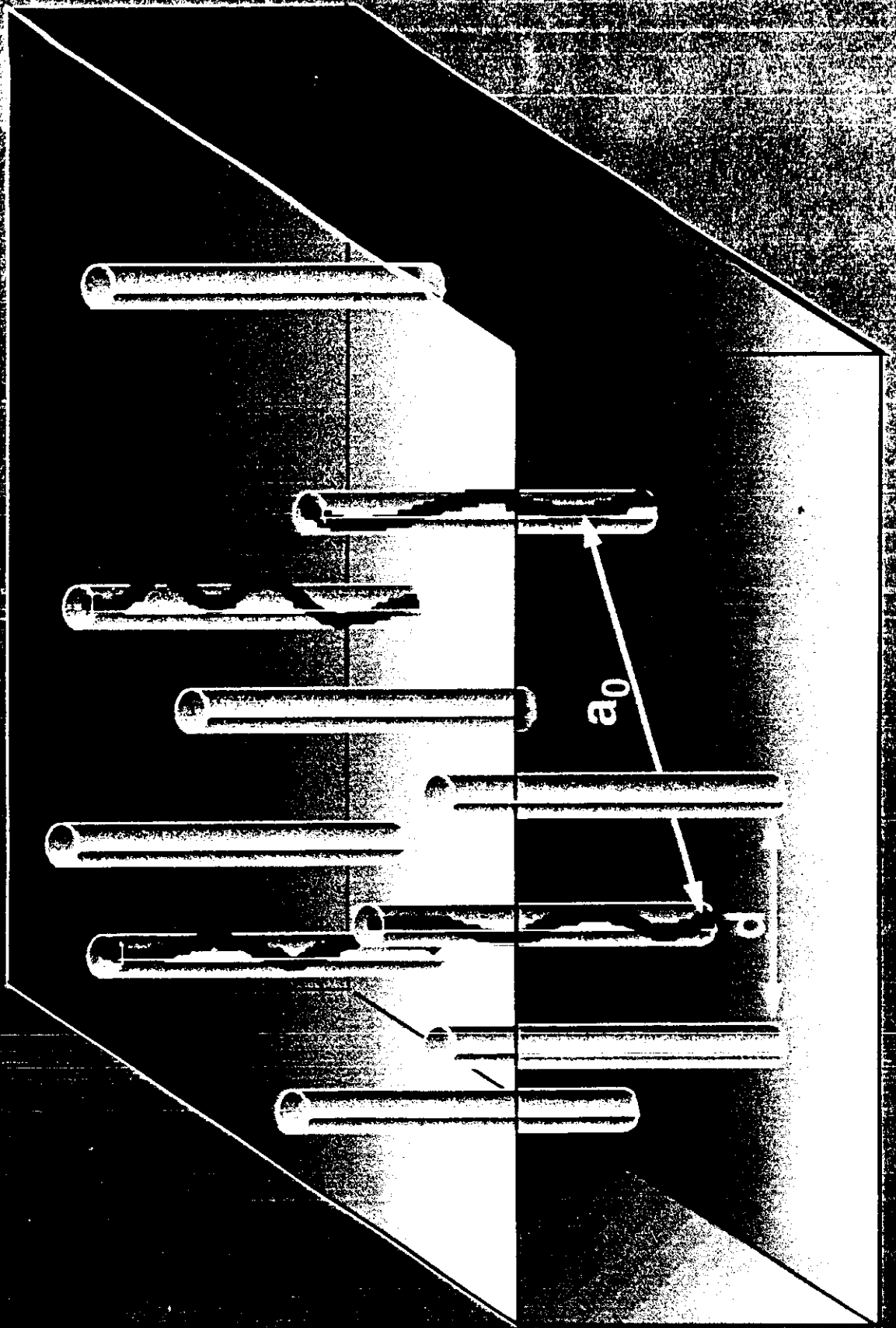
Charge ↔ ϕ_0

\vec{E} ↔ $\hat{x} \times \vec{J} / c$

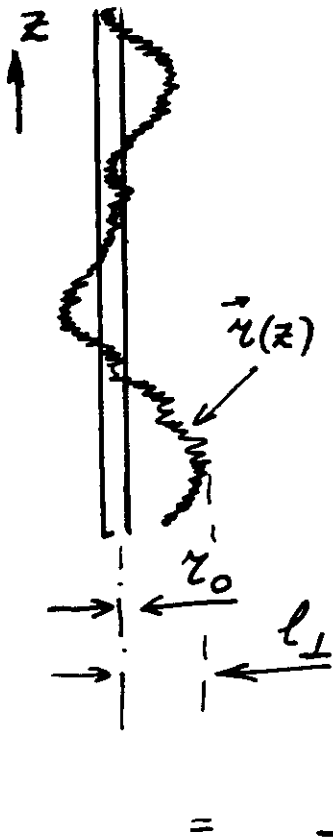
J/c ↔ \vec{E}

σ ↔ ρ

BOSE GLASS



CRITICAL CURRENTS

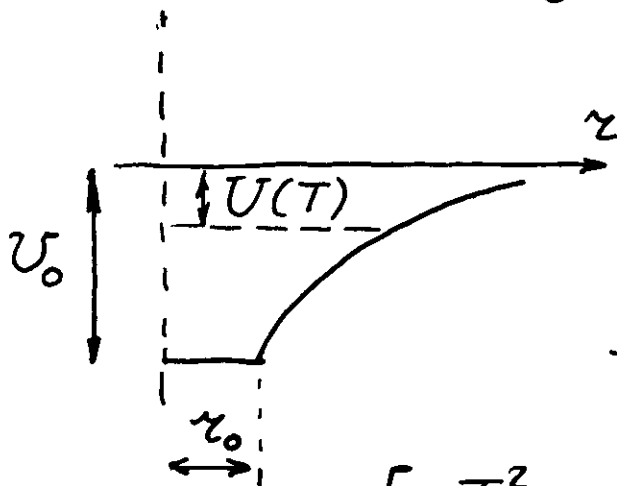


a vortex line trapped near a single columnar pin $\parallel z$

The binding free energy

$$U(T) = U_0 - TS$$

$$\exp [U(T)L/T] = \frac{\int \mathcal{D}\vec{r}(z) \exp \left[-\frac{1}{T} \int_0^L dz \left(\frac{\epsilon_1}{2} \left(\frac{d\vec{r}}{dz} \right)^2 + V_D(\vec{r}(z)) \right) \right]}{\int \mathcal{D}\vec{r}(z) \exp \left[-\frac{1}{T} \int_0^L dz \frac{\epsilon_1}{2} \left(\frac{d\vec{r}}{dz} \right)^2 \right]}$$



In the limit $L \rightarrow \infty$ the smallest eigenvalue dominates and

$$U(T) = -E_0$$

$$\left[-\frac{T}{2\epsilon_1} \nabla^2 + V_D(\vec{r}) \right] \Psi_0(\vec{r}) = E_0 \Psi_0(\vec{r})$$

$$V_D(z) \cong \frac{U_0 z_0^2}{r_0^2 + z^2}$$

(G.S. Mkrtchyan and V.V. Schmidt, Sov. Phys. JETP 34, 195 (1972))

$$U(T) \approx U_0 e^{-T/T^*}$$

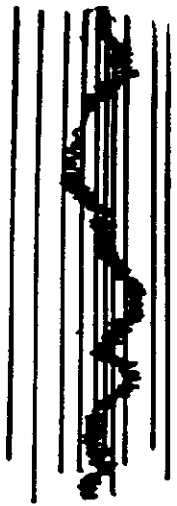
$$T^* \approx \frac{\sqrt{2}}{\pi} \kappa_0 \sqrt{\epsilon_2 U_0} : \text{'depinning' energy}$$

$$l_{\perp} \approx \kappa_0 \frac{T}{T^*} e^{T/2T^*}$$

$$j_c \approx j_0 \frac{\kappa_0^2}{3^2} \frac{T^*}{T} \exp\left(-\frac{3}{2} \frac{T}{T^*}\right)$$

↑
pair breaking current

$$T \gg T_1 = T^* \ln(d^2/\kappa_0^2)$$



$$l_{\perp} > d$$

$$l_{\perp} \approx d \left(\frac{T}{T_1}\right)^2$$

$$U(T) \approx U_0 \left(\frac{\kappa_0}{d}\right)^2 \left(\frac{T_1}{T}\right)^2$$

$$j_c \approx j_0 \left(\frac{\kappa_0}{d}\right)^2 \left(\frac{T_1}{T}\right)^4 \frac{\kappa_0}{d}$$

Point defects

Let us assume that vortex lines are bound by some effective '2D' potential.

Binding energy:

$$|E| \sim \exp\left(-\frac{\hbar^2}{m|U_{\text{eff}}|^{1/3}}\right) \rightarrow \exp\left(-\frac{T^2}{\epsilon_L |U_{\text{eff}}|^{1/3}}\right)$$

Find $|U_{\text{eff}}|$:

$$\sqrt{\gamma L_2} \sim T \qquad |U_{\text{eff}}| \sim \frac{T}{L_2} \sim \frac{\gamma}{T}$$

↑
strength
of the pinning
potential

$$\left[l_{\perp} \approx \epsilon_L \frac{l_{\perp}^2}{L_2} \sim T \right]$$

$$E \sim \exp\left(-\frac{T^3}{\epsilon_L \gamma^{1/3}}\right)$$

$$\text{cf. } j_c \sim \exp\left[-\left(\frac{T}{T_{dp}}\right)^3\right]$$

$$T_{dp} \approx (\epsilon_L \gamma^{1/3})^{1/3}$$

[M.V. Feigel'man
& Vinokur, PR B 41, 8986 (1990)]

BOSE GLASS TRANSITION

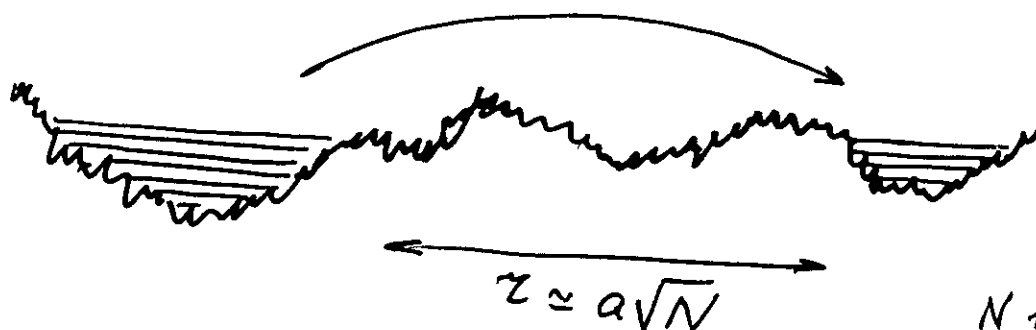
BOSE GLASS PHASE:
 VORTICES LOCALIZED
 NEAR COLUMNAR
 DEFECTS

QM
 \longleftrightarrow
 MAPPING

2D BOSONS ARE
 LOCALIZED
 BY THE QUENCHED
 2D DISORDER

THE GLASS TRANSITION LINE
 IS OBTAINED AS THE TRANSITION FROM THE
 LOCALIZED INTO THE SUPERFLUID STATE IN THE
 RELATED BOSE SYSTEM AT ZERO TEMPERATURE

DILUTE LIMIT $a \gg \lambda$ ($a \approx \sqrt{\Phi_0 / B}$)



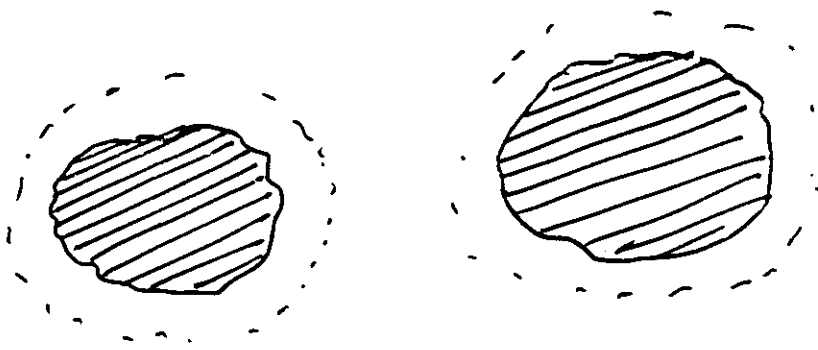
N is the number
 of the particles
 in the each well

GLASS-TO-LIQUID TRANSITION:
 SEQUENTIAL FILLING OF THE POTENTIAL
 WELLS GENERATED BY DISORDER

THE RELATED QM SYSTEM IS A WEAKLY NONIDEAL GAS
 OF HARD CORE 2D BOSONS WITH INTERACTIONS DESCRIBED BY

$$g = \frac{1}{2.9\pi} \frac{g_0}{1 + g_0 \ln(1/\lambda^2 n_v)}$$

$$g_0 = \frac{\epsilon_l \epsilon_0}{2\pi T^2} \int dz z V(z) = \frac{\epsilon_l \epsilon_0 \lambda^2}{2\pi T^2}$$



THE TRANSFER OF A PARTICLE
FROM ONE DROPLET TO ANOTHER INCREASES THE
TOTAL ENERGY BY $2gE$

HOWEVER, SUCH AN EXCHANGE INCREASES
THE POSITIONAL ENTROPY AND THE CORRESPONDING
GAIN IN THE FREE ENERGY IS $E \exp(-\gamma/\ell)$

$$[\ell = T^2 / (\Delta_1)^{1/2} \epsilon_\ell]$$

$$\Delta_1 = \frac{U_0^2 \gamma_0^4}{d^2}$$

UPON INCREASING THE DEGREE OF FILLING THE DISTANCE
BETWEEN THE DROPLETS DECREASES, THE VORTEX STATES
BECOME MORE EXTENDED, AND THE PERCOLATION-LIKE
TRANSITION INTO A SUPERFLUID STATE (VORTEX LIQUID)
OCCURS.

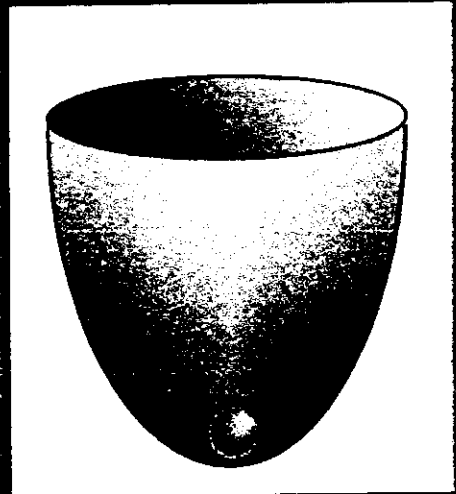
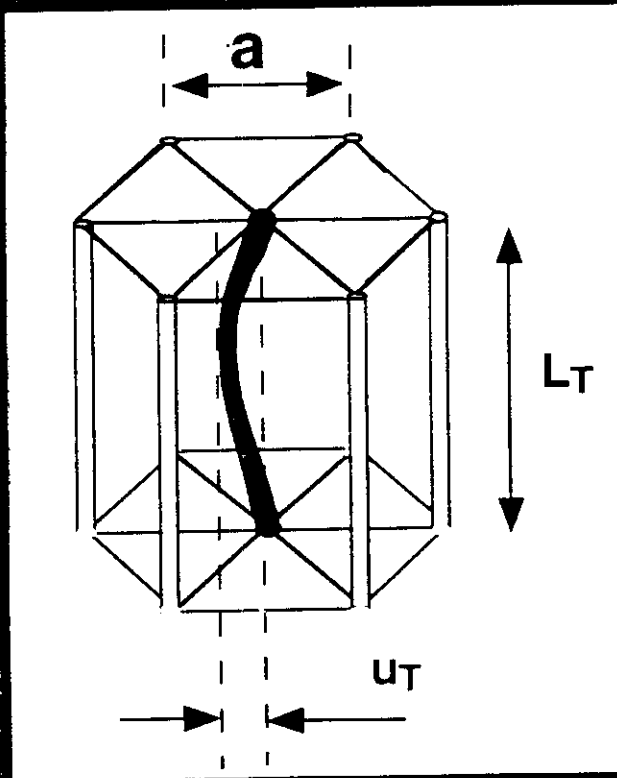
THE TRANSITION LINE: $E \exp(-\frac{\gamma}{\ell}) = gE$

$$\Rightarrow B_{BG} = \frac{\Phi_0}{\ell^2} \mathcal{L} \cong B_\Phi \left(\frac{T^*}{T}\right)^4 \propto (T_c - T)^4$$

$$\mathcal{L} = \frac{\ln(1/\lambda^2 n_v)}{[\ln \ln(1/\lambda^2 n_v)]^2} \quad (g \ll 1), \quad \mathcal{L} \approx 1 \quad (g \approx 1)$$

g is the coupling
const.

BOSE GLASS TRANSITION



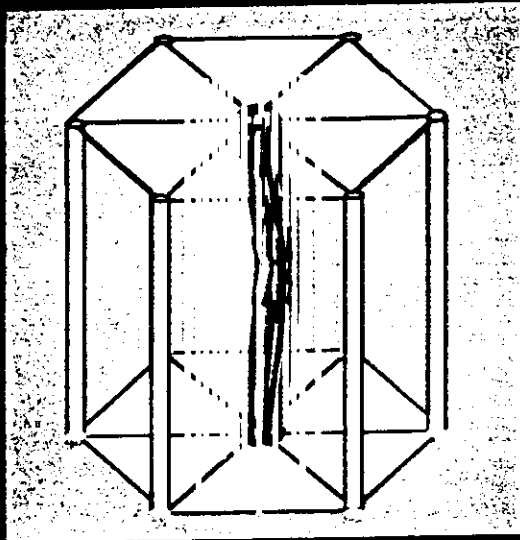
$$E_{el} = c_{66} u^2 L + \epsilon_l (u^2 / L)$$

$$L_T = \sqrt{\epsilon_l / c_{66}} \quad u_T^2 = T / \sqrt{\epsilon_l c_{66}}$$

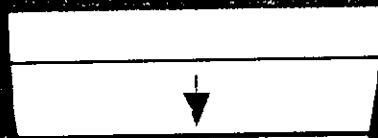
MELTING:

$$T \cong E_b$$

$$= c_L^2 c_{66} a^2 L_T$$

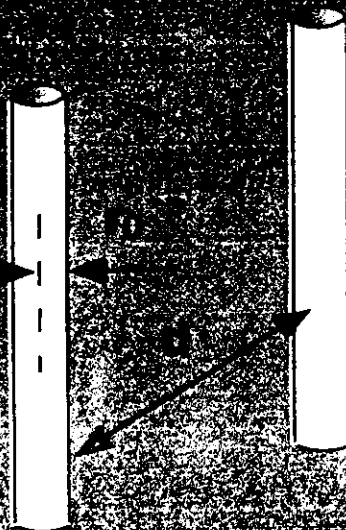


$$E_p = L_T \sqrt{\Delta / (u_T^2 + \xi^2)}$$



$$T = c_L^2 c_{66} a^2 L_T + L_T \sqrt{\Delta / (u_T^2 + \xi^2)}$$

$$T_{BG} = T_m \left[1 + \frac{\pi^2 c_L^2 a (T^*)^2}{2 d T_m^2} \right]$$



$$T_{BG} = L_T \sqrt{\Delta / (u_T^2 + \xi^2)}$$

$$B_{BG} \cong 4\Phi_0 \varepsilon_\ell^2 \Delta / T^6 \propto (T_c - T)^6$$

$$T^* = (2 / \sqrt{\pi}) r_0 \sqrt{\varepsilon_\ell U_0}$$

ALTERNATIVE APPROACH:

→ FROM THE LIQUID

DISORDER-INDUCED RENORMALISATION OF THE TILT MODULUS:

$$\frac{1}{C_{44}^{UR}} = \frac{1}{C_{44}^V} - \frac{T^4 n_v \Delta_1}{(C_{44}^V)^2 \epsilon_1} \int \frac{d^2 q q^4}{\epsilon^4(q)}$$

[T. Hwa et al.,
PRL 71, 3545
(1993);
and to be published]

where $\epsilon(q)$ represents the spectrum of
the 2D related bosons

vortex related part of the tilt modulus
becomes infinite at the Bose glass
transition line

Test:

in the dilute limit, $\lambda < a$,

$$\epsilon(q) = \left[\frac{T^4 q^4}{(2\epsilon_1)^2} + \frac{4\pi T^4 n_v q^2}{\epsilon_1^2 \ln(n_v \lambda^2)} \right]^{1/2}$$

⇒

$$B_{BG} \approx B_\phi \left(\frac{T^*}{T}\right)^4 \mathcal{L}$$

$$\mathcal{L} = \frac{\ln(1/\lambda^2 n_v)}{[\ln \ln(1/\lambda^2 n_v)]^2}$$

which coincides up to a
log factor with the transition
found from the condition $l_\perp \approx a$

DENSE LIMIT, $a < \lambda$,

interpolation formula

$$\varepsilon^2(q) = T^2 \omega_p^2 - \frac{2\varepsilon_0 T^2 q^2}{\pi \varepsilon_1} + \frac{(Tq)^4}{(2\varepsilon_1)^2}$$

[cf M.V. Feigelman et al
PRB 48, 16641
(1993)]

$$\omega_p^2 = \frac{4\pi n \varepsilon_0}{\varepsilon_1}$$

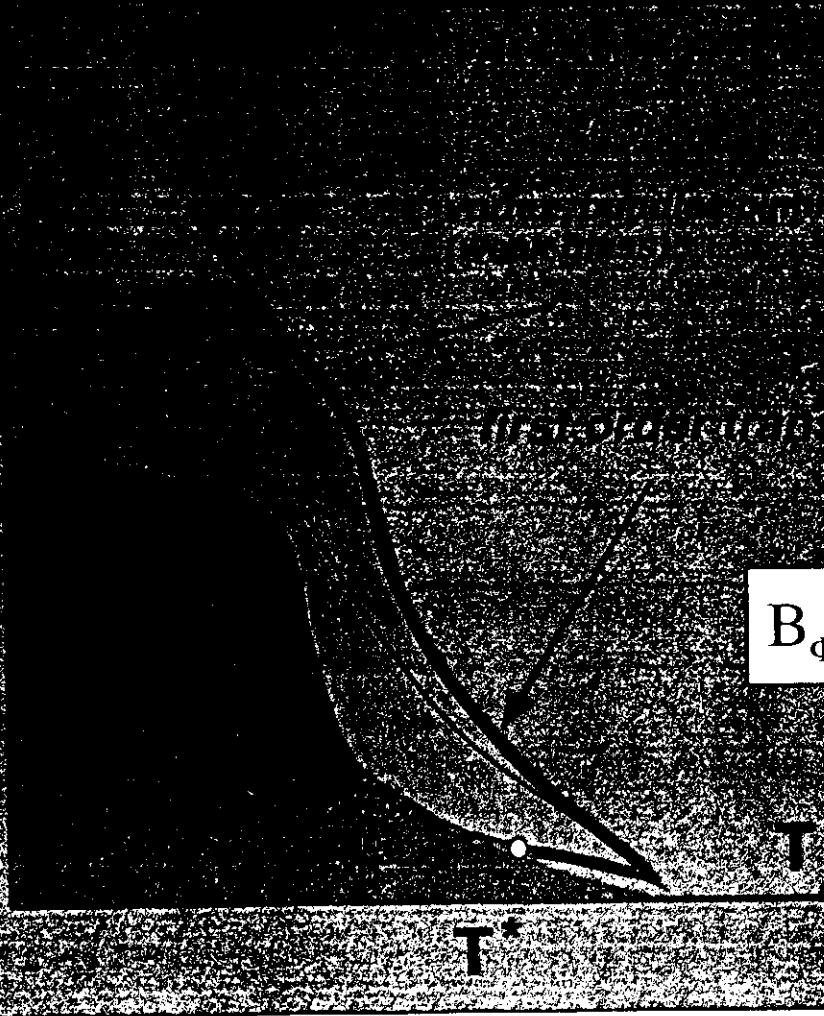
$$(\varepsilon_1 \leftrightarrow m, e^2 \leftrightarrow \varepsilon_0)$$

$$\varepsilon_0 = \frac{\Phi_0^2}{(4\pi\lambda)^2} \quad \varepsilon_1 = \varepsilon^2 \varepsilon_0$$

$$\Rightarrow B_{BG} \simeq \frac{4\Phi_0 \varepsilon_1^2 \Delta}{T^6}$$

SCHEMATIC PHASE DIAGRAM FOR SUPERCONDUCTORS WITH COLUMNAR DEFECTS

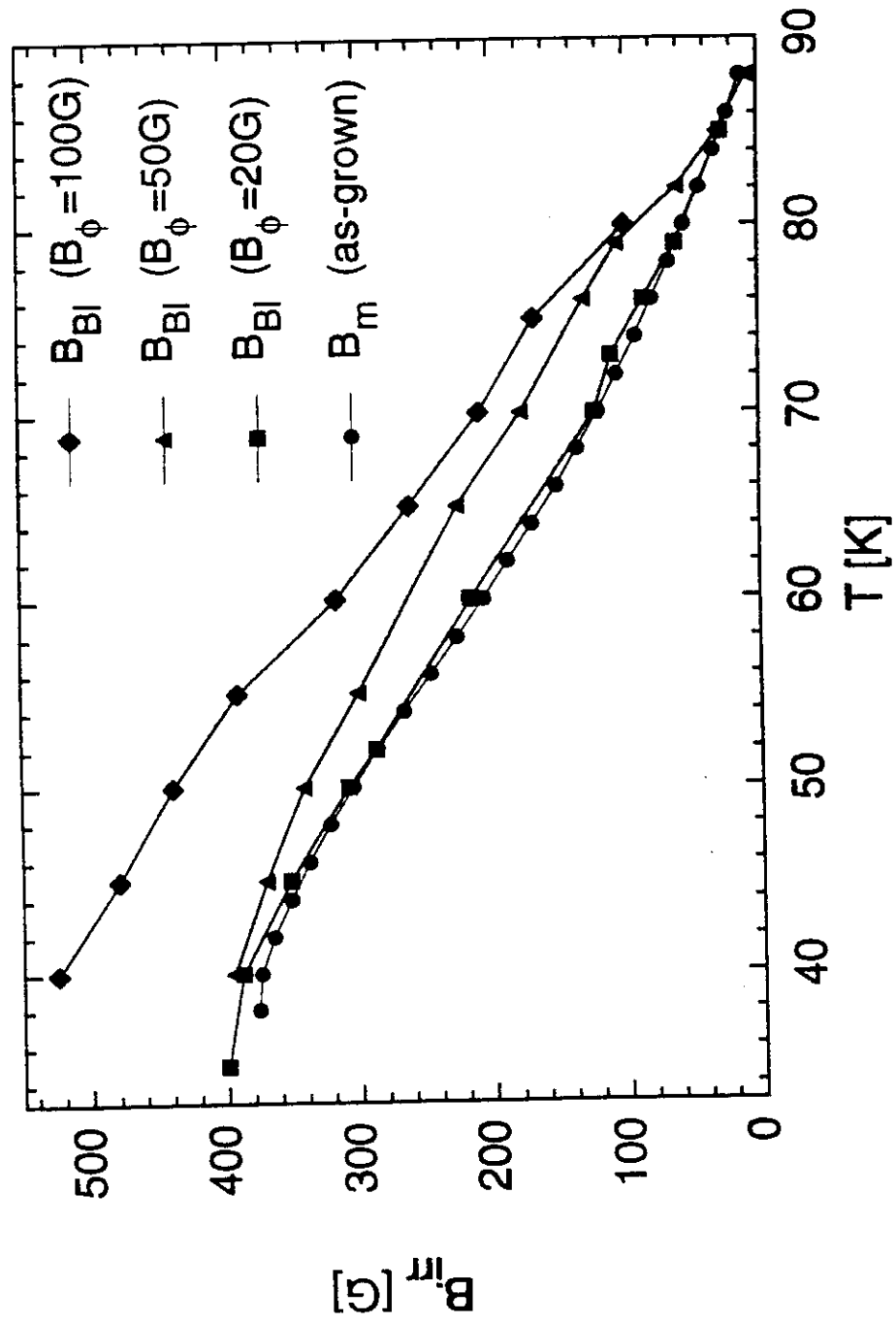
$$B_{\Phi} > B_m(T^*)$$



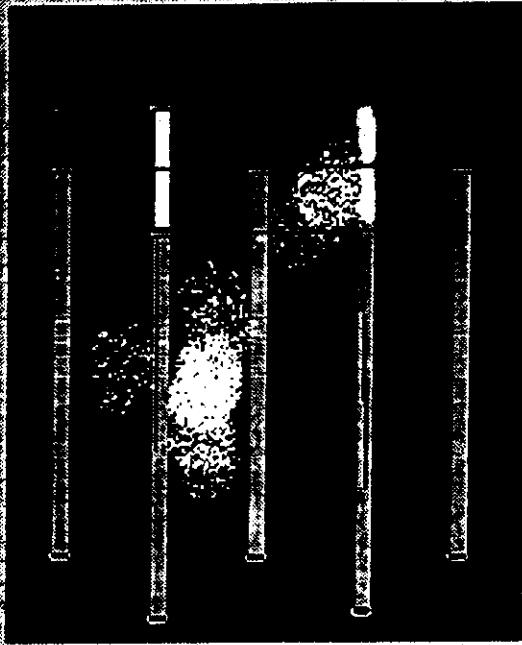
$$B_{\Phi} < B_m(T^*)$$

Onset of bulk pinning in BSCCO crystal irradiated

by heavy ions with different doses



DISORDER-FIELD-DRIVEN TRANSITION



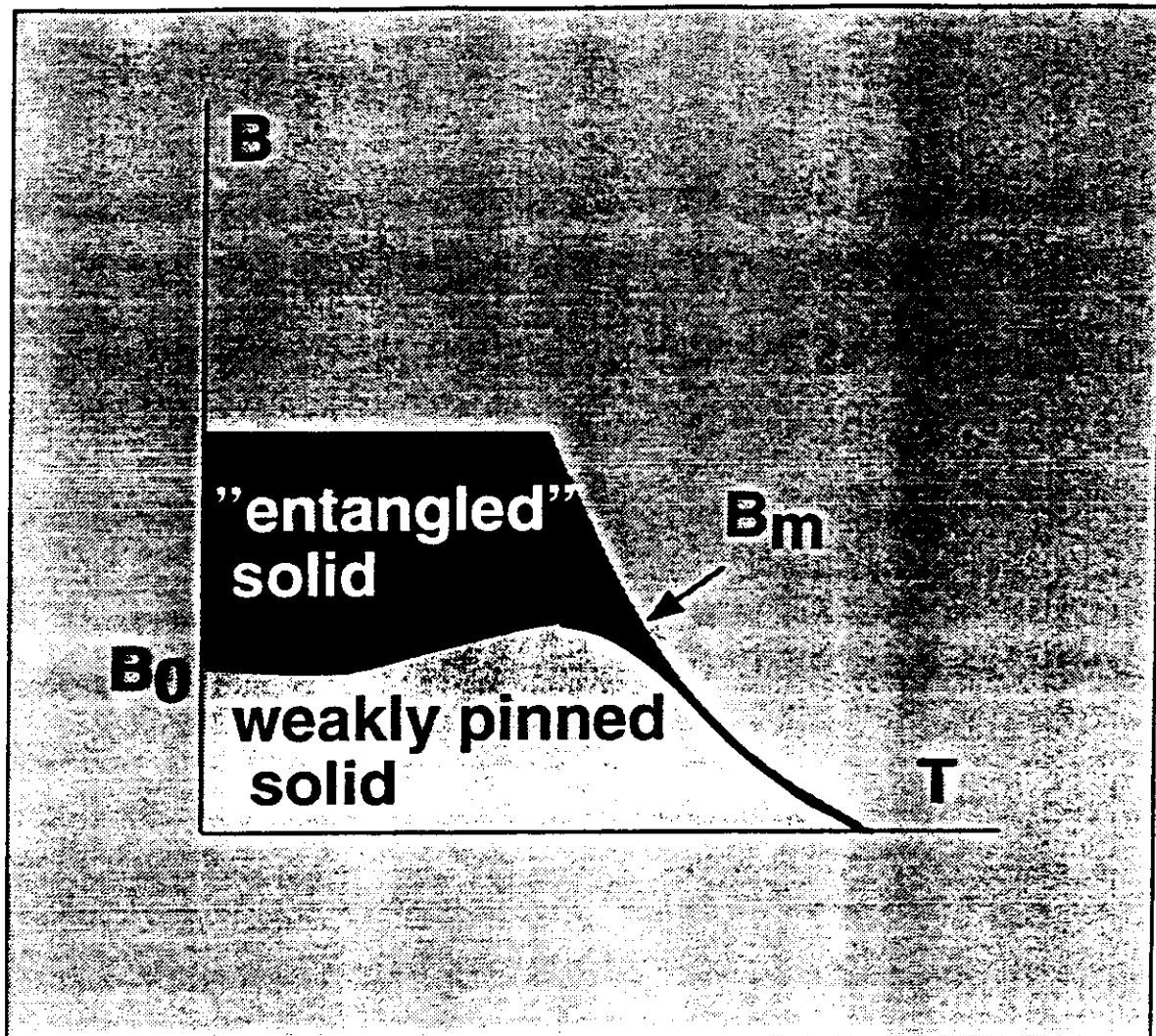
$$c_L^2 C_{66} a^2 L_T = \sqrt{\gamma} L_T$$

$$L_T = 2 \epsilon a$$

$$\frac{B_0}{H_{c2}} = \frac{c_L^8 \epsilon^6}{2\pi} \left(\frac{\epsilon_0 \xi}{T_{dp}} \right)^6$$

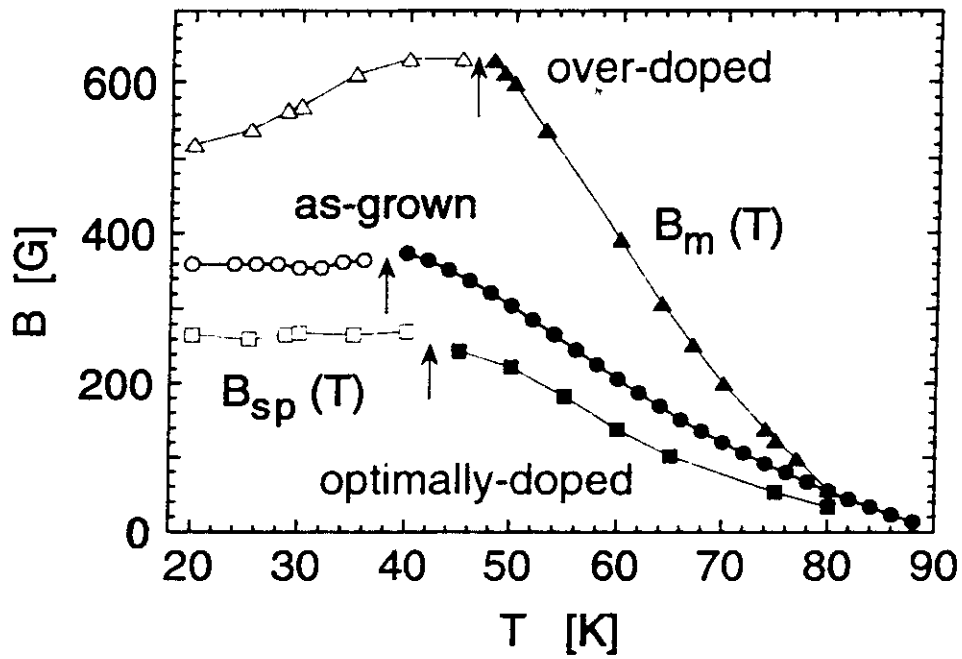
$$B_0 \approx 1.5 \cdot 10^5 \left(\frac{4}{T_{dp}} \right)^6$$

D. ERTAŞ & D. NELSON

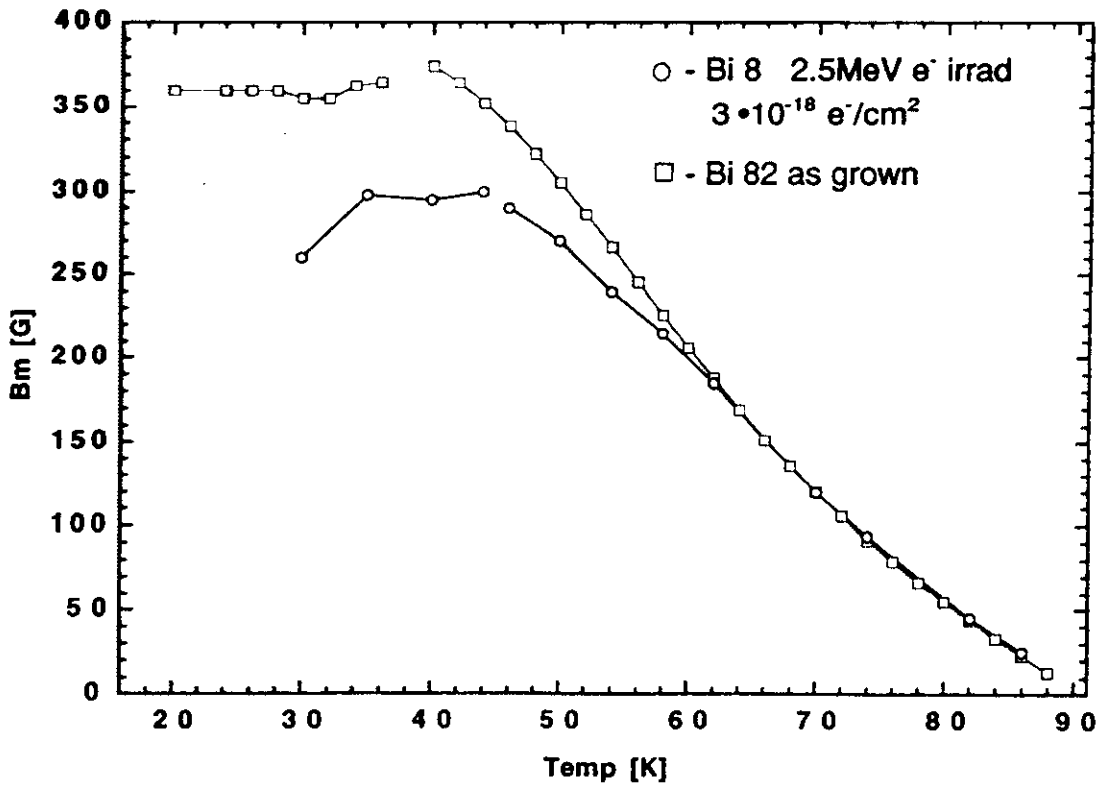


$$c_L^2 c_{66} a^2 L_T = \sqrt{\frac{8L_T}{1 + \langle u_T^2 \rangle / 3^2}} + T$$

BSCCO melting and second peak lines different anisotropy crystals



Melting transition line in BSCCO



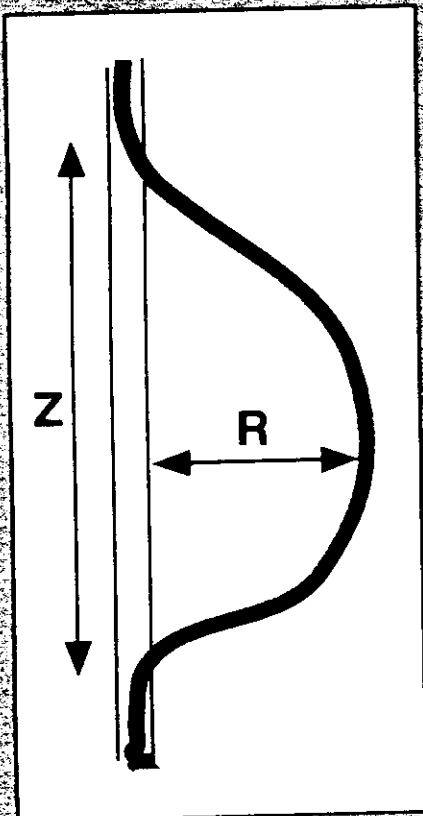
CREEP FROM THE SINGLE WELL

One flux-line free energy:
$$F = \int dz \left[\frac{\epsilon_l}{2} \left(\frac{dR}{dz} \right)^2 + V_D(R(z)) - f_L R(z) \right]$$

$$f_L = \frac{J}{c} \Phi_0, \quad J_1 < J < J_2, \quad f_L = \frac{cU_0}{\Phi_0 d}$$

d is the distance between pins

The energy change (due to formation of the half loop) relative to the case $f_L = 0$:



$$\delta F \approx \frac{\epsilon_l R^2}{Z} + U_0 Z - f_L RZ$$

cost in elastic energy

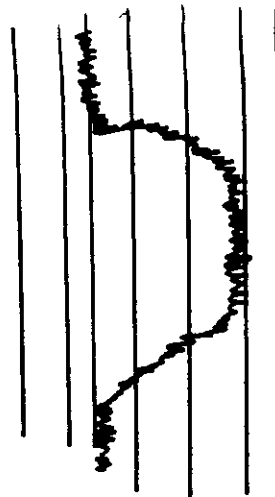
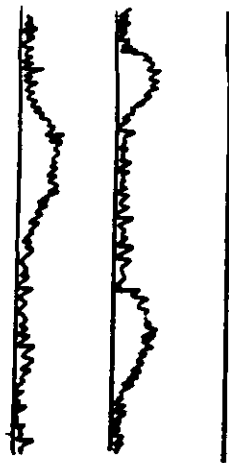
pinning energy

gain in energy due to applied current

Optimization with respect to R and Z :

$$R^* = \sqrt{\frac{U_0}{\epsilon_l}} Z^* = \frac{cU_0}{J\Phi_0}$$

$$\delta F^* = \frac{c\epsilon_l^{1/2} U_0^{3/2}}{J\Phi_0}$$



The 'half loop' excitations are relevant at high current densities where the critical nucleus does not get reach out to the neighboring columns

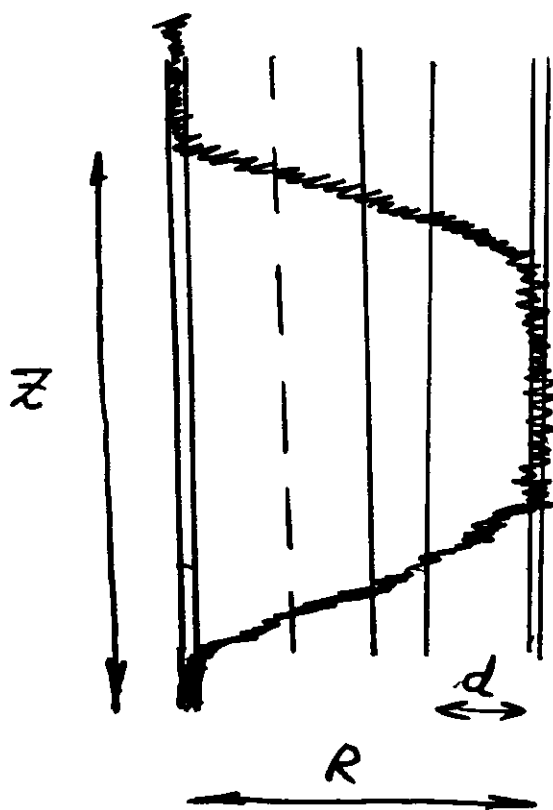
Current decreases, and double-kink excitations to the neighboring track become relevant

Dispersion in the pinning energies becomes important for small current densities

(VRH)

$$\mathcal{E} \propto \exp(-\text{const} / J^{1/3})$$

VRH REGIME



$$\delta F(R, z) \approx$$

$$2E_K \frac{R}{d} +$$

$$+ \frac{z}{gR^2} - f_L R z$$

Kink energy:

$$E_K \approx d\sqrt{\epsilon_2 U_0}$$

$$f_L = \frac{1}{c} \Phi_0 J$$

The characteristic energy difference between the initial and final vortex states:

the total number of states with energy within ΔE of this flux line at distances less than or equal to R is $g \Delta E R^2$ (g is the density of states)

By setting $g \Delta E R^2 \approx 1$, find $\Delta E \approx 1/gR^2$

$$\delta F^* \approx \frac{E_K}{d} \left(\frac{c}{g \Phi_0 J} \right)^{1/3} \rightarrow \mathcal{O} \propto \exp \left[-\frac{E_K}{T} \left(\frac{J_{VRH}}{J} \right)^{1/3} \right]$$

$$J_{VRH} = \frac{c}{\Phi_0 g d^3}$$

vortex velocity:

$$v \sim \exp\left(-\frac{c \epsilon_i^{1/2} U_0^{3/2}}{J \Phi_0 T}\right)$$



Cold emission:

$$W \approx \exp\left[-\frac{4\sqrt{2}}{3} \frac{U_0^{3/2} m^{1/2}}{\hbar \epsilon e}\right]$$

Electric field

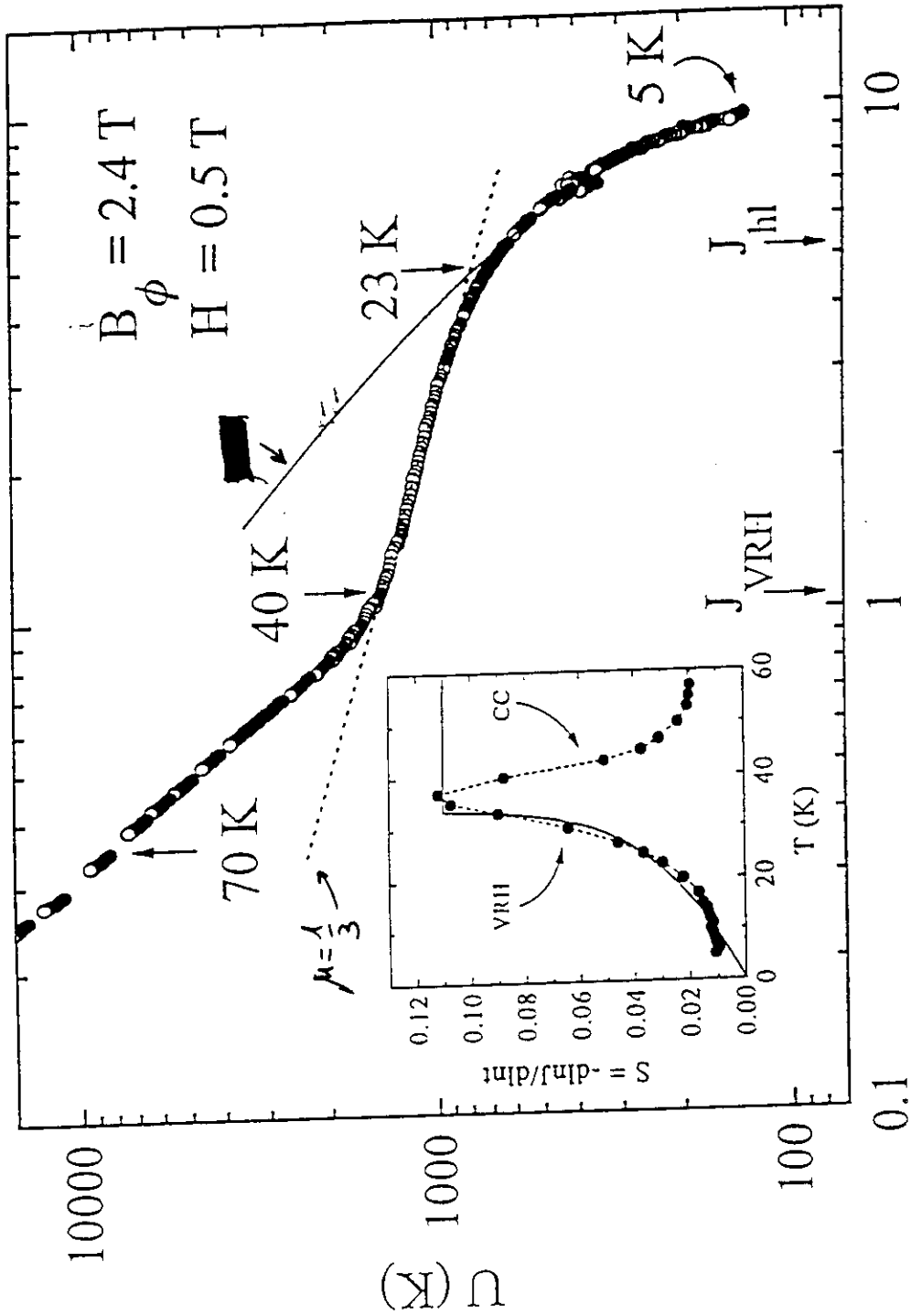


Fig 4

CONCLUSIONS

- PHYSICS OF FLUX LINES IS MAPPED ONTO THE PROBLEM OF LOCALIZATION OF QUANTUM MECHANICAL BOSONS IN TWO DIMENSIONS
- PHASE DIAGRAM FOR THE BOSE- AND VORTEX GLASSES IS CONSTRUCTED
- FIRST ORDER TRANSITION LINES TERMINATE AT CRITICAL POINTS
- THE IRREVERSIBILITY LINE DUE TO COLUMNAR DEFECTS SHIFTS UPWARDS AS COMPARED TO THE MELTING LINE IN CLEAN SYSTEMS
- TEMPERATURE DEPENDENCE OF THE CRITICAL CURRENTS IS FOUND
- NON-TRIVIAL CREEP REGIME : VARIABLE RANGE VORTEX HOPPING IS PREDICTED

